

NTLJF3118N

Power MOSFET and Schottky Diode

20 V, 4.6 A, N-Channel, with 2.0 A Schottky Barrier Diode, 2x2 mm WDFN Package



ON Semiconductor®

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Features

- WDFN 2x2 mm Package Provides Exposed Drain Pad for Excellent Thermal Conduction
- Footprint Same as SC-88 Package
- 1.8 V V_{GS} Rated $R_{DS(on)}$
- Low Profile (< 0.8 mm) for Easy Fit in Thin Environments
- Low V_F 2 A Schottky Diode
- This is a Pb-Free Device

Applications

- DC-DC Boost/Buck Converter
- Low Voltage Hard Disk DC Power Source

MAXIMUM RATINGS ($T_J = 25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Value	Unit	
Drain-to-Source Voltage	V_{DSS}	20	V	
Gate-to-Source Voltage	V_{GS}	± 12	V	
Continuous Drain Current (Note 1)	Steady State	$T_A = 25^\circ\text{C}$	3.8	A
		$T_A = 85^\circ\text{C}$	2.8	
		$t \leq 5 \text{ s}$	$T_A = 25^\circ\text{C}$	
Power Dissipation (Note 1)	Steady State	$T_A = 25^\circ\text{C}$	1.5	W
		$t \leq 5 \text{ s}$	2.2	
Continuous Drain Current (Note 2)	Steady State	$T_A = 25^\circ\text{C}$	2.6	A
		$T_A = 85^\circ\text{C}$	1.9	
Power Dissipation (Note 2)	Steady State	$T_A = 25^\circ\text{C}$	0.7	W
Pulsed Drain Current	$t_p = 10 \mu\text{s}$	I_{DM}	18	A
Operating Junction and Storage Temperature	T_J, T_{STG}	-55 to 150	$^\circ\text{C}$	
Source Current (Body Diode)	I_S	1.8	A	
Lead Temperature for Soldering Purposes (1/8" from case for 10 s)	T_L	260	$^\circ\text{C}$	

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

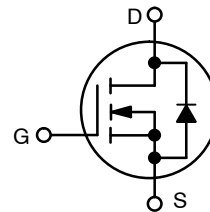
1. Surface Mounted on FR4 Board using 2 in sq pad size (Cu area = 1.127 in sq [2 oz] including traces).
2. Surface Mounted on FR4 Board using the minimum recommended pad size.

MOSFET

$V_{(BR)DSS}$	$R_{DS(on)}$ Max	I_D Max
20 V	65 m Ω @ 4.5 V	3.8 A
	85 m Ω @ 2.5 V	2.0 A
	120 m Ω @ 1.8 V	1.7 A

SCHOTTKY DIODE

V_R Max	V_F Typ	I_F Max
20 V	0.41 V	2.0 A



N-CHANNEL MOSFET

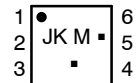


SCHOTTKY DIODE



WDFN6 CASE 506AN

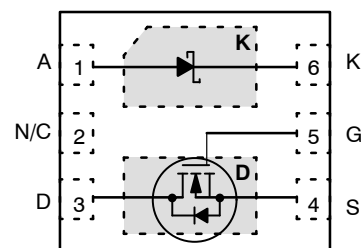
MARKING DIAGRAM



- JK = Specific Device Code
- M = Date Code
- = Pb-Free Package

(Note: Microdot may be in either location)

PIN CONNECTIONS



(Top View)

ORDERING INFORMATION

See detailed ordering and shipping information on page 3 of this data sheet.

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SCHOTTKY DIODE MAXIMUM RATINGS ($T_J = 25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Value	Unit
Peak Repetitive Reverse Voltage	V_{RRM}	20	V
DC Blocking Voltage	V_R	20	V
Average Rectified Forward Current	I_F	2.0	A

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

THERMAL RESISTANCE RATINGS

Parameter	Symbol	Max	Unit
Junction-to-Ambient – Steady State (Note 3)	$R_{\theta JA}$	83	$^\circ\text{C}/\text{W}$
Junction-to-Ambient – $t \leq 5$ s (Note 3)	$R_{\theta JA}$	58	
Junction-to-Ambient – Steady State Min Pad (Note 4)	$R_{\theta JA}$	177	

3. Surface Mounted on FR4 Board using 2 in sq pad size (Cu area = 1.127 in sq [2 oz] including traces).

4. Surface Mounted on FR4 Board using the minimum recommended pad size.

MOSFET ELECTRICAL CHARACTERISTICS ($T_J = 25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
OFF CHARACTERISTICS						
Drain-to-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS} = 0$ V, $I_D = 250$ μA	20			V
Drain-to-Source Breakdown Voltage Temperature Coefficient	$V_{(BR)DSS}/T_J$	$I_D = 250$ μA , Ref to 25°C		10.4		$\text{mV}/^\circ\text{C}$
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 16$ V, $V_{GS} = 0$ V			1.0	μA
					10	
Gate-to-Source Leakage Current	I_{GSS}	$V_{DS} = 0$ V, $V_{GS} = \pm 8.0$ V			± 100	nA

ON CHARACTERISTICS (Note 5)

Gate Threshold Voltage	$V_{GS(TH)}$	$V_{GS} = V_{DS}$, $I_D = 250$ μA	0.4	0.7	1.0	V
Gate Threshold Temperature Coefficient	$V_{GS(TH)}/T_J$			-3.0		$\text{mV}/^\circ\text{C}$
Drain-to-Source On-Resistance	$R_{DS(on)}$	$V_{GS} = 4.5$ V, $I_D = 3.8$ A		37	65	m Ω
		$V_{GS} = 2.5$ V, $I_D = 2.0$ A		46	85	
		$V_{GS} = 1.8$ V, $I_D = 1.7$ A		65	120	
Forward Transconductance	g_{FS}	$V_{DS} = 10$ V, $I_D = 1.7$ A		4.2		S

CHARGES, CAPACITANCES AND GATE RESISTANCE

Input Capacitance	C_{ISS}	$V_{GS} = 0$ V, $f = 1$ MHz, $V_{DS} = 10$ V		271		pF
Output Capacitance	C_{OSS}			72		
Reverse Transfer Capacitance	C_{RSS}			43		
Total Gate Charge	$Q_{G(TOT)}$	$V_{GS} = 4.5$ V, $V_{DS} = 10$ V, $I_D = 3.8$ A		3.7		nC
Threshold Gate Charge	$Q_{G(TH)}$			0.3		
Gate-to-Source Charge	Q_{GS}			0.6		
Gate-to-Drain Charge	Q_{GD}			1.0		

SWITCHING CHARACTERISTICS (Note 6)

Turn-On Delay Time	$t_{d(ON)}$	$V_{GS} = 4.5$ V, $V_{DD} = 16$ V, $I_D = 1.0$ A, $R_G = 2.0$ Ω		3.8		ns
Rise Time	t_r			4.7		
Turn-Off Delay Time	$t_{d(OFF)}$			11.1		
Fall Time	t_f			5.8		

DRAIN-SOURCE DIODE CHARACTERISTICS

Forward Diode Voltage	V_{SD}	$V_{GS} = 0$ V, $I_S = 1.0$ A	$T_J = 25^\circ\text{C}$		0.69	1.0	V
Reverse Recovery Time	t_{RR}	$V_{GS} = 0$ V, $dI_S/dt = 100$ A/ μs , $I_S = 1.0$ A			10.2		ns

5. Pulse Test: Pulse Width ≤ 300 μs , Duty Cycle $\leq 2\%$.

6. Switching characteristics are independent of operating junction temperatures.

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SCHOTTKY DIODE ELECTRICAL CHARACTERISTICS ($T_J = 25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Maximum Instantaneous Forward Voltage	V_F	$I_F = 0.1\text{ A}$		0.26	0.35	V
		$I_F = 1.0\text{ A}$		0.35	0.42	
		$I_F = 2.0\text{ A}$		0.41	0.52	
Maximum Instantaneous Reverse Current	I_R	$V_R = 20\text{ V}$		0.20	5.0	mA
		$V_R = 10\text{ V}$		0.045	1.0	

SCHOTTKY DIODE ELECTRICAL CHARACTERISTICS ($T_J = 85^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Maximum Instantaneous Forward Voltage	V_F	$I_F = 0.1\text{ A}$		0.18		V
		$I_F = 1.0\text{ A}$		0.29		
		$I_F = 2.0\text{ A}$		0.36		
Maximum Instantaneous Reverse Current	I_R	$V_R = 20\text{ V}$		4.9		mA
		$V_R = 10\text{ V}$		1.6		

SCHOTTKY DIODE ELECTRICAL CHARACTERISTICS ($T_J = 125^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Maximum Instantaneous Forward Voltage	V_F	$I_F = 0.1\text{ A}$		0.13		V
		$I_F = 1.0\text{ A}$		0.25		
		$I_F = 2.0\text{ A}$		0.33		
Maximum Instantaneous Reverse Current	I_R	$V_R = 20\text{ V}$		42		mA
		$V_R = 10\text{ V}$		13		

SCHOTTKY DIODE ELECTRICAL CHARACTERISTICS ($T_J = 25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Capacitance	C	$V_R = 5.0\text{ V}$, $f = 1.0\text{ MHz}$		52.3		pF

ORDERING INFORMATION

Device	Package	Shipping [†]
NTLJF3118NTAG	WDFN6 (Pb-Free)	3000 / Tape & Reel
NTLJF3118NTBG	WDFN6 (Pb-Free)	3000 / Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

NTLJF3118N

TYPICAL N-CHANNEL PERFORMANCE CURVES ($T_J = 25^\circ\text{C}$ unless otherwise noted)

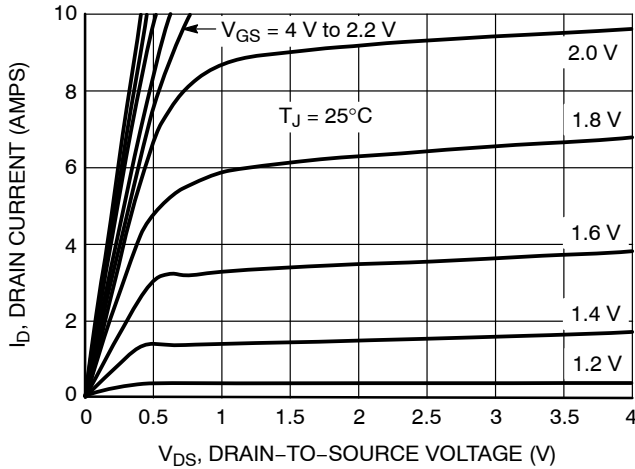


Figure 1. On-Region Characteristics

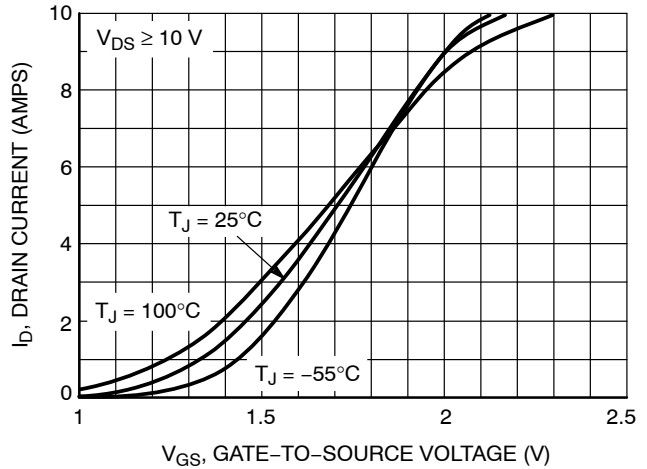


Figure 2. Transfer Characteristics

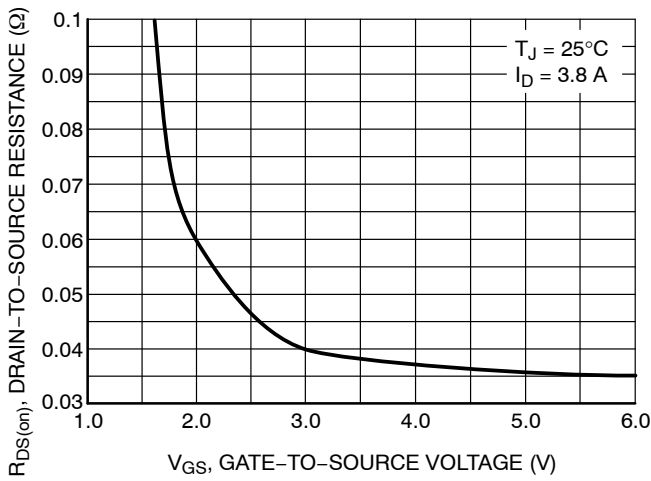


Figure 3. On-Resistance versus Drain Current

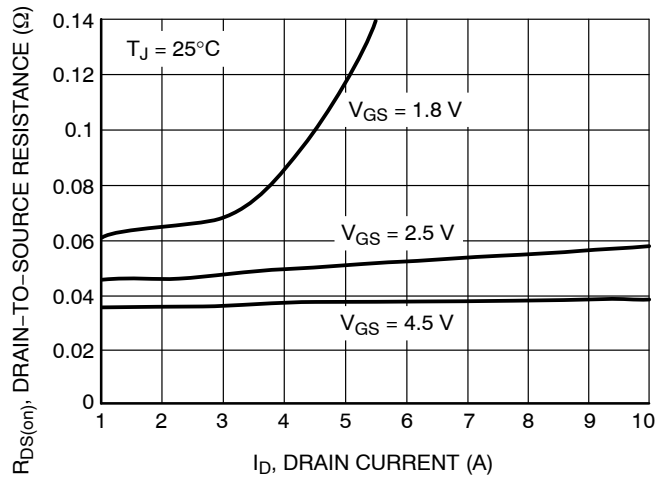


Figure 4. On-Resistance versus Drain Current and Gate Voltage

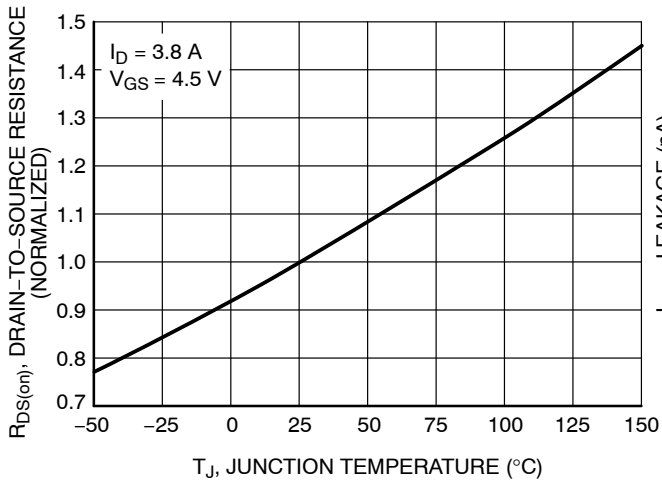


Figure 5. On-Resistance Variation with Temperature

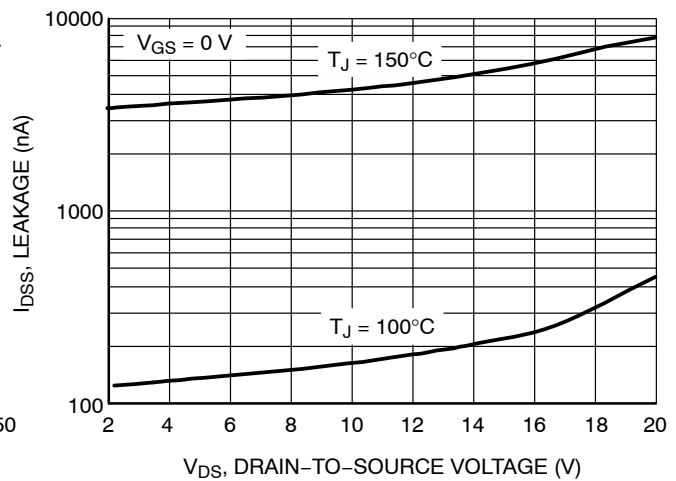


Figure 6. Drain-to-Source Leakage Current versus Voltage

TYPICAL N-CHANNEL PERFORMANCE CURVES ($T_J = 25^\circ\text{C}$ unless otherwise noted)

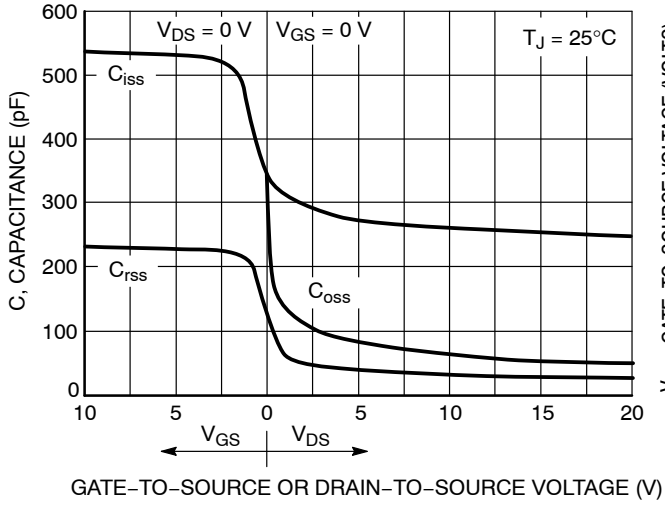


Figure 7. Capacitance Variation

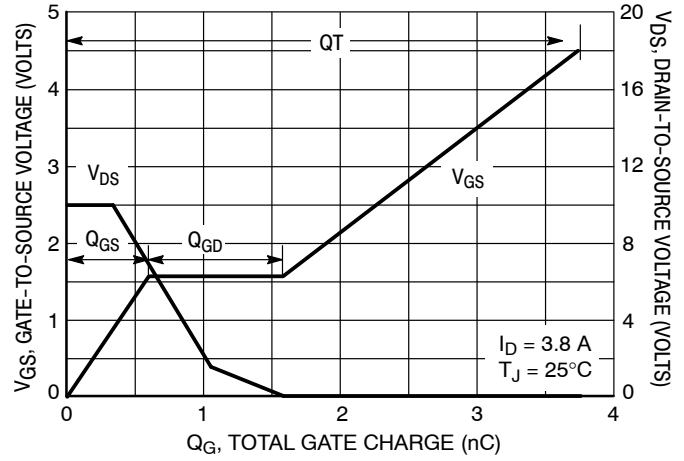


Figure 8. Gate-To-Source and Drain-To-Source Voltage versus Total Charge

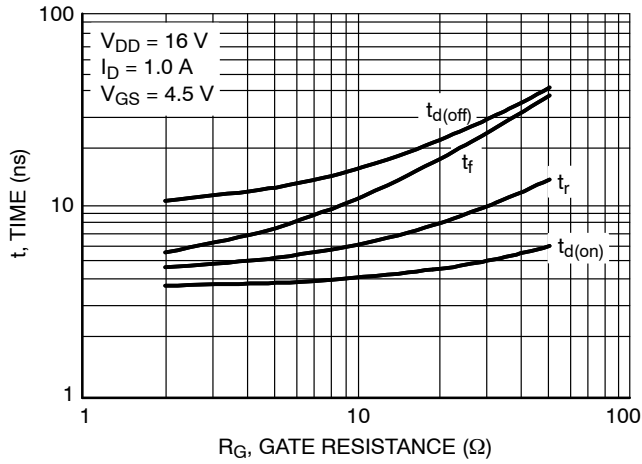


Figure 9. Resistive Switching Time Variation versus Gate Resistance

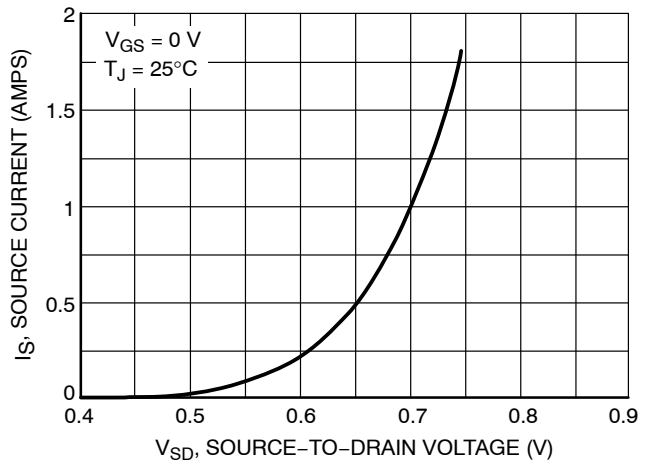


Figure 10. Diode Forward Voltage versus Current

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TYPICAL SCHOTTKY PERFORMANCE CURVES ($T_J = 25^\circ\text{C}$ unless otherwise noted)

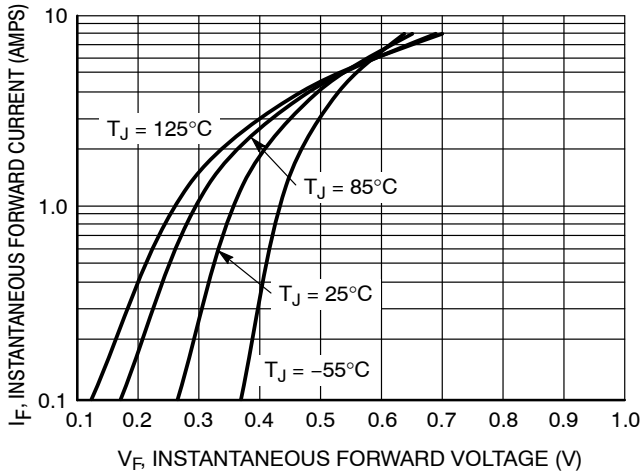


Figure 11. Typical Forward Voltage

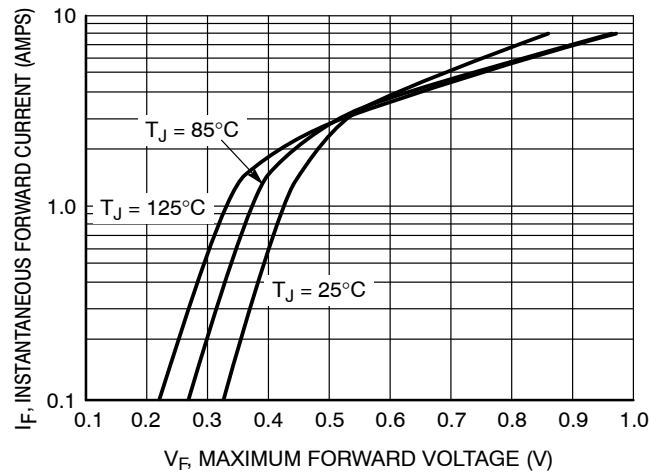


Figure 12. Maximum Forward Voltage

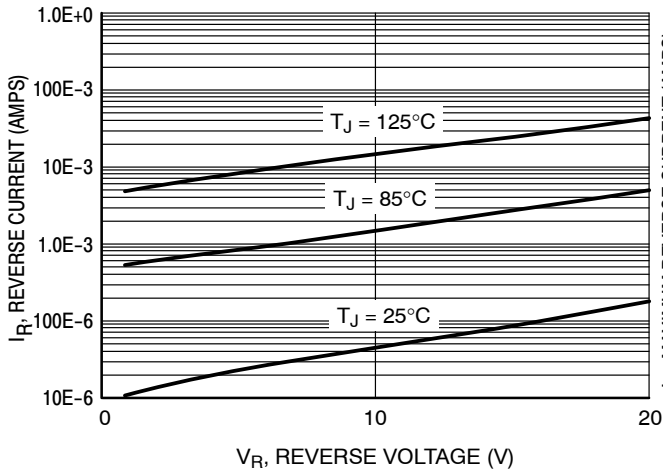


Figure 13. Typical Reverse Current

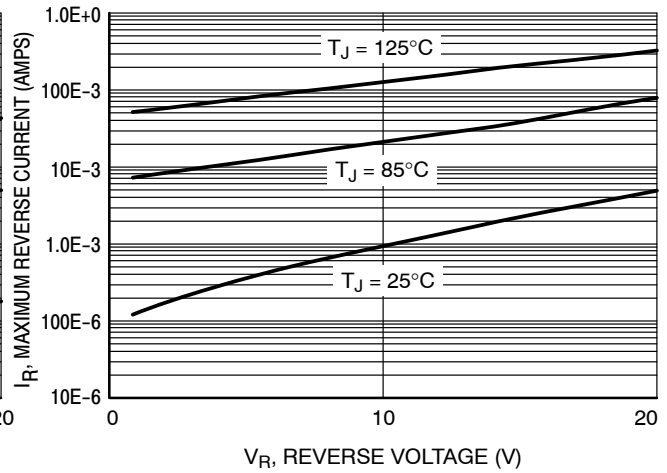
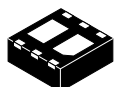


Figure 14. Maximum Reverse Current

MECHANICAL CASE OUTLINE

PACKAGE DIMENSIONS

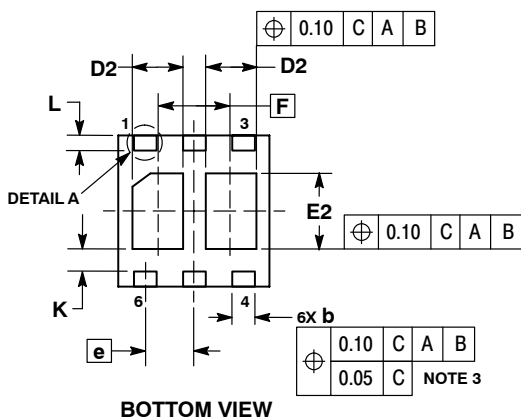
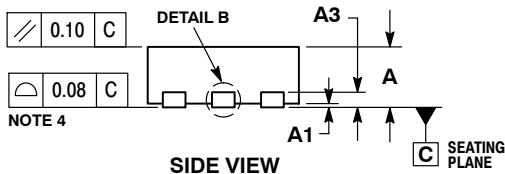
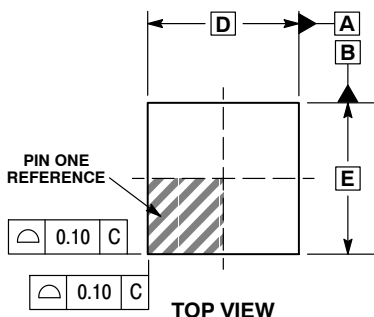
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SCALE 4:1

WDFN6 2x2, 0.65P
CASE 506AN
ISSUE G

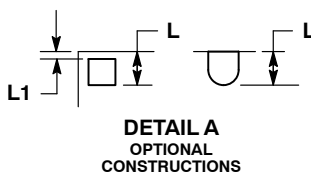
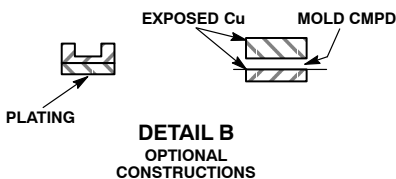
DATE 22 AUG 2013



STYLE 1:
PIN 1. SOURCE 1
2. GATE 1
3. DRAIN 2
4. SOURCE 2
5. GATE 2
6. DRAIN 1

STYLE 2:
PIN 1. ANODE
2. N/C
3. DRAIN
4. SOURCE
5. GATE
6. CATHODE

STYLE 3:
PIN 1. SOURCE 1
2. GATE 1
3. SOURCE 2
4. DRAIN 2
5. GATE 2
6. DRAIN 1

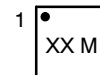


NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. DIMENSION b APPLIES TO PLATED TERMINAL AND IS MEASURED BETWEEN 0.15 AND 0.30 mm FROM THE TERMINAL TIP.
4. COPLANARITY APPLIES TO THE EXPOSED PAD AS WELL AS THE TERMINALS.

DIM	MILLIMETERS	
	MIN	MAX
A	0.70	0.80
A1	0.00	0.05
A3	0.20 REF	
b	0.25	0.35
D	2.00 BSC	
D2	0.57	0.77
E	2.00 BSC	
E2	0.90	1.10
e	0.65 BSC	
F	0.95 BSC	
K	0.25 REF	
L	0.20	0.30
L1	---	0.10

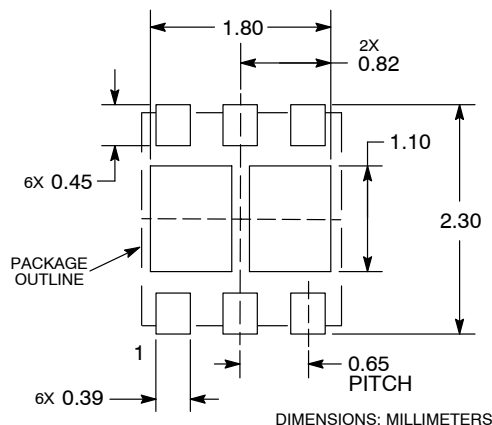
GENERIC MARKING DIAGRAM*



XX = Specific Device Code
M = Date Code

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "μ", may or may not be present.

SOLDERMASK DEFINED MOUNTING FOOTPRINT



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DESCRIPTION:	WDFN6 2X2, 0.65P	PAGE 1 OF 1

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